MMBFJ309L, MMBFJ310L, SMMBFJ309L, SMMBFJ309L

JFET - VHF/UHF Amplifier Transistor

N-Channel

Features

- Drain and Source are Interchangeable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	25	Vdc
Gate-Source Voltage	V _{GS}	25	Vdc
Gate Current	I _G	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

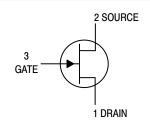
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.



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SOT-23 (TO-236) CASE 318 STYLE 10

MARKING DIAGRAM



6x = Device Code

x = U for MMBFJ309L, SMMBFJ309L x = T for MMBFJ310L, SMMBFJ310L

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBFJ309LT1G,	SOT-23	3,000 / Tape &
SMMBFJ309LT1G	(Pb-Free)	Reel
MMBFJ310LT1G,	SOT-23	3,000 / Tape &
SMMBFJ310LT1G	(Pb-Free)	Reel
SMMBFJ310LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBFJ309L, MMBFJ310L, SMMBFJ309L, SMMBFJ310L

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	1		•	•	
Gate–Source Breakdown Voltage $(I_G = -1.0 \mu Adc, V_{DS} = 0)$	V _{(BR)GSS}	-25	-	-	Vdc
Gate Reverse Current ($V_{GS} = -15 \text{ Vdc}$) ($V_{GS} = -15 \text{ Vdc}$, $T_A = 125^{\circ}\text{C}$)	I _{GSS}	_ _	- -	-1.0 -1.0	nAdc μAdc
Gate Source Cutoff Voltage MMBFJ30 (V _{DS} = 10 Vdc, I _D = 1.0 nAdc) MMBFJ310, SMMBFJ37	GG(011)	-1.0 -2.0	- -	-4.0 -6.5	Vdc
ON CHARACTERISTICS					
	500	12 24	_ _	30 60	mAdc
Gate–Source Forward Voltage (I _G = 1.0 mAdc, V _{DS} = 0)	V _{GS(f)}	_	-	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS	:	•	•	•	
Forward Transfer Admittance (V _{DS} = 10 Vdc, I _D = 10 mAdc, f = 1.0 kHz)	Y _{fs}	8.0	-	18	mmhos
Output Admittance (V _{DS} = 10 Vdc, I _D = 10 mAdc, f = 1.0 kHz)	ly _{os} l	-	-	250	μmhos
Input Capacitance (V _{GS} = -10 Vdc, V _{DS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	-	-	5.0	pF
Reverse Transfer Capacitance (V _{GS} = -10 Vdc, V _{DS} = 0 Vdc, f = 1.0 MHz)	C _{rss}	-	_	2.5	pF
Equivalent Short–Circuit Input Noise Voltage (V _{DS} = 10 Vdc, I _D = 10 mAdc, f = 100 Hz)	e _n	-	10	-	nV/√Hz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

MMBFJ309L, MMBFJ310L, SMMBFJ309L, SMMBFJ310L

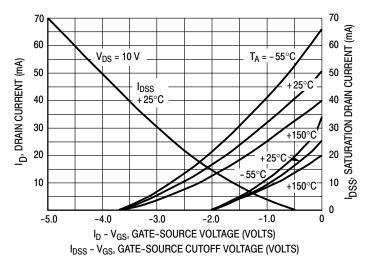


Figure 1. Drain Current and Transfer Characteristics versus Gate-Source Voltage

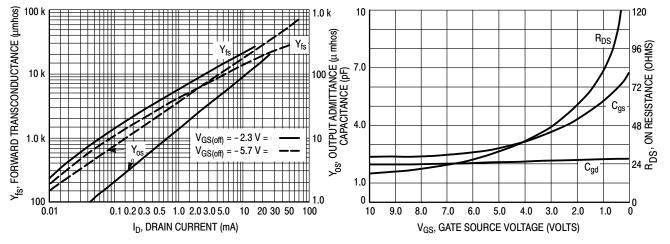


Figure 2. Common–Source Output
Admittance and Forward Transconductance
versus Drain Current

Figure 3. On Resistance and Junction Capacitance versus Gate-Source Voltage

MMBFJ309L, MMBFJ310L, SMMBFJ309L, SMMBFJ310L

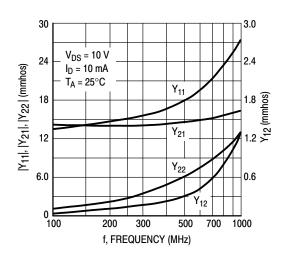


Figure 4. Common-Gate Y Parameter Magnitude versus Frequency

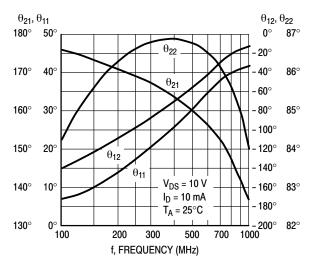


Figure 6. Common–Gate Y Parameter Phase–Angle versus Frequency

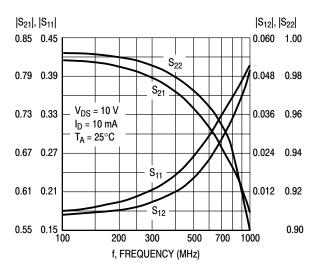


Figure 5. Common-Gate S Parameter Magnitude versus Frequency

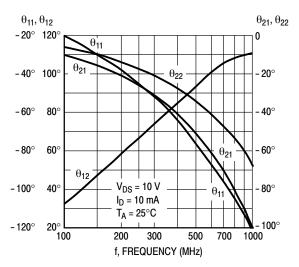


Figure 7. S Parameter Phase–Angle versus Frequency





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NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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